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High Voltage Surface Mount Input Rectifier Diode, 10 A



PRIMARY CHARACTERISTICS								
I _{F(AV)}	10 A							
V _R	800 V, 1000 V, 1200 V							
V _F at I _F	1.1 V							
I _{FSM}	160 A							
T _J max.	150 °C							
Package	D ² PAK (TO-263AB)							
Circuit configuration	Single							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Glass passivated pellet chip junction
- Designed and qualified according to JEDEC[®]-JESD 47



 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification
- Vishay switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-10ETS..S-M3 rectifier series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
Capacitive input filter T _A = 55 °C, T _J = 125 °C common heatsink of 1 °C/W	12.0	16.0	А						

MAJOR RATIN	MAJOR RATINGS AND CHARACTERISTICS										
SYMBOL	CHARACTERISTICS	VALUES	UNITS								
I _{F(AV)}	Sinusoidal waveform	10	A								
V _{RRM}		800 to 1200	V								
I _{FSM}		160	A								
V _F	10 A, T _J = 25 °C	1.1	V								
TJ		-40 to +150	°C								

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 ℃ mA						
VS-10ETS08S-M3	800	900							
VS-10ETS10S-M3	1000	1100	0.5						
VS-10ETS12S-M3	1200	1300							

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum average forward current	I _{F(AV)}	$T_C = 105 \ ^{\circ}C$, 180° conduction half sine wave	10						
Maximum peak one cycle	1	10 ms sine pulse, rated V _{RRM} applied	135	A					
non-repetitive surge current	IFSM	10 ms sine pulse, no voltage reapplied	160						
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	91	A ² s					
Maximum r-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	130	A-5					
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	1290	A²√s					

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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST (VALUES	UNITS		
Maximum forward voltage drop	V _{FM}	10 A, T _J = 25 °C		1.1	V	
Forward slope resistance	r _t	T.I = 150 °C	20	mΩ		
Threshold voltage	V _{F(TO)}	1J = 150 C	0.82	V		
Maximum reverse leakage current	1	T _J = 25 °C	V _B = rated V _{BBM}	0.05	mA	
Maximum reverse leakage current	I _{RM}	T _J = 150 °C	$v_{\rm R}$ = rated $v_{\rm RRM}$	0.50	ША	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.5	°C/W					
Maximum thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		62	0/10					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
			10ET	S08S					
Marking device		Case style D ² PAK (TO-263AB)	10ETS10S						
			10ET	S12S					

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994

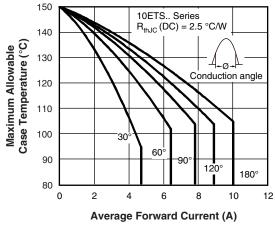


Fig. 1 - Current Rating Characteristics

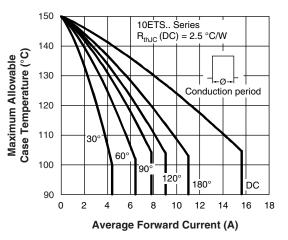
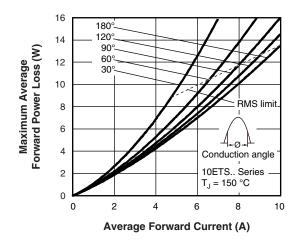


Fig. 2 - Current Rating Characteristics

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Fig. 3 - Forward Power Loss Characteristics

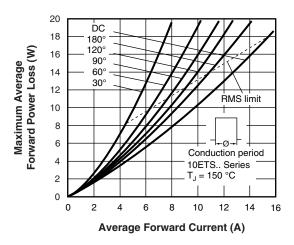


Fig. 4 - Forward Power Loss Characteristics

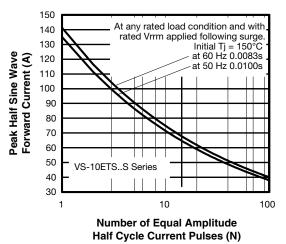


Fig. 5 - Maximum Non-Repetitive Surge Current

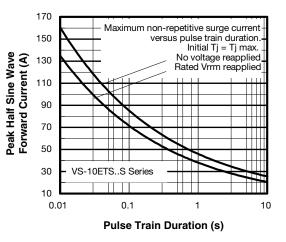


Fig. 6 - Maximum Non-Repetitive Surge Current

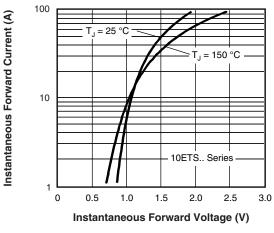
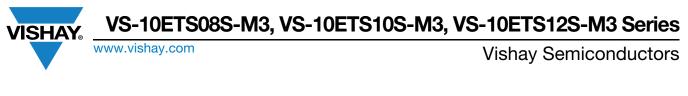


Fig. 7 - Forward Voltage Drop Characteristics

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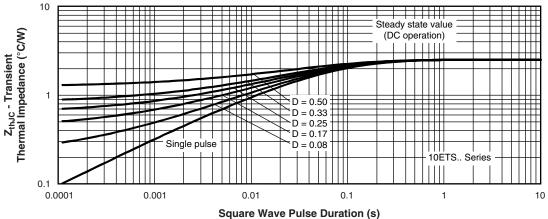


Fig. 8 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	10	Е	т	s	12	S	TRL	-МЗ
	1	2	3	4	5	6	7	8	9
	1	- Visl	hay Sen	nicondut	tors pro	duct			
	2 -	Cur	rent rati	ng (10 =	= 10 A)				
	3 -	Circ	uit conf	iguratior	า:				
		E	= single	•					
	4 -	Pac	kage:						
	_	Т	= D ² PA	K (TO-2	63AB)				
	5 -	Тур	e of silio	con:					
			= stand		-		Γ	08 = 80	
	6 -		age coo			1		10 = 10 12 = 12	
	7 -		surface		able		L	12 - 12	00 V
	8 -		one = tu						
			RL = tap						
			RR = tap						
	9	M	3 = halo	gen-free	e, RoHS	-compli	ant, and	d termin	ations I

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ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-10ETS08S-M3	50	Antistatic plastic tube							
VS-10ETS08STRR-M3	800	13" diameter reel							
VS-10ETS08STRL-M3	800	13" diameter reel							
VS-10ETS10S-M3	50	Antistatic plastic tube							
VS-10ETS10STRR-M3	800	13" diameter reel							
VS-10ETS10STRL-M3	800	13" diameter reel							
VS-10ETS12S-M3	50	Antistatic plastic tube							
VS-10ETS12STRR-M3	800	13" diameter reel							
VS-10ETS12STRL-M3	800	13" diameter reel							
VS-10ETS08S-M3	50	Antistatic plastic tube							

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					

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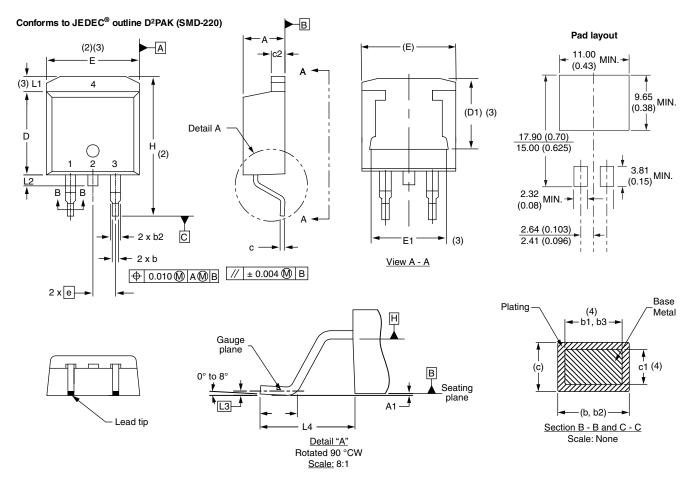


Outline Dimensions

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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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